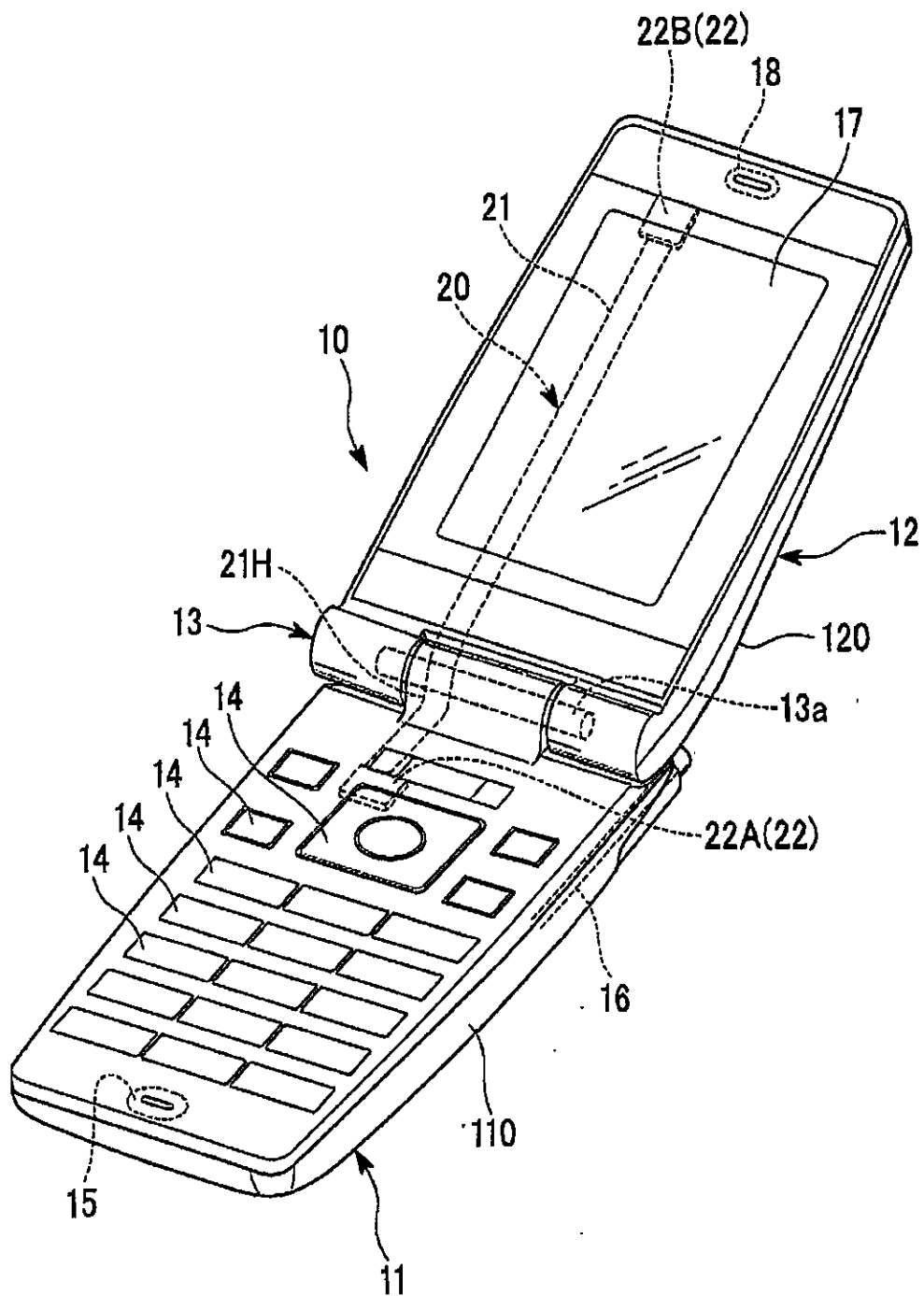


FIG. 1



A cross-sectional view of a semiconductor device 21. The device consists of a substrate 21a, a first conductive layer 21b, and a second conductive layer 21c. The device is divided into regions 21f and 21d. The first conductive layer 21b is located on the substrate 21a, and the second conductive layer 21c is located on the first conductive layer 21b. The regions 21f and 21d are defined by the layout of the conductive layers.

FIG. 4

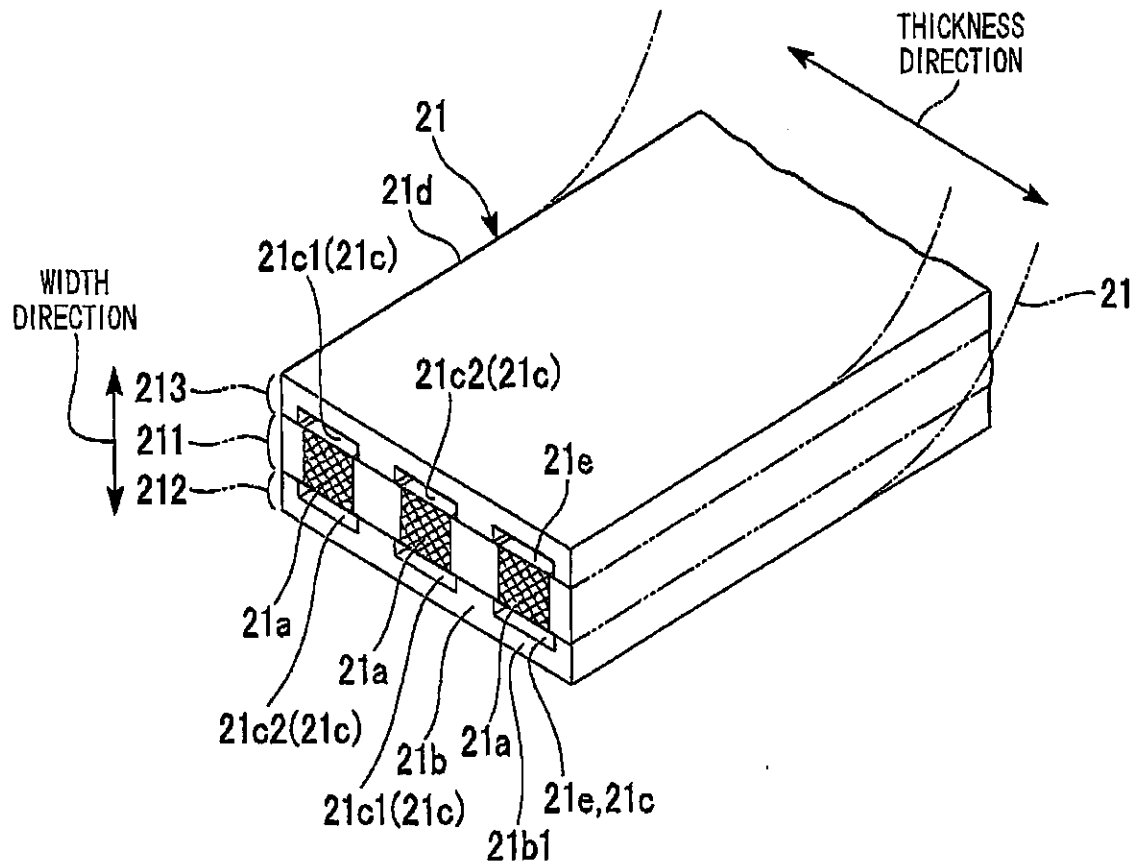


FIG. 5

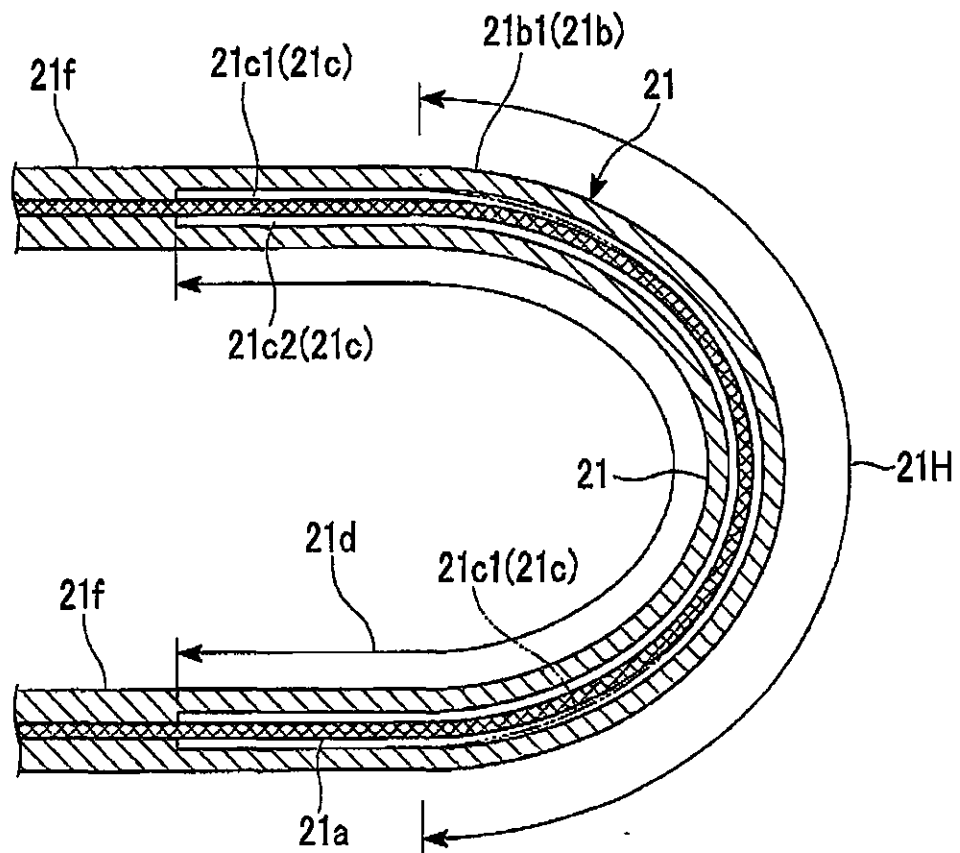


FIG. 6

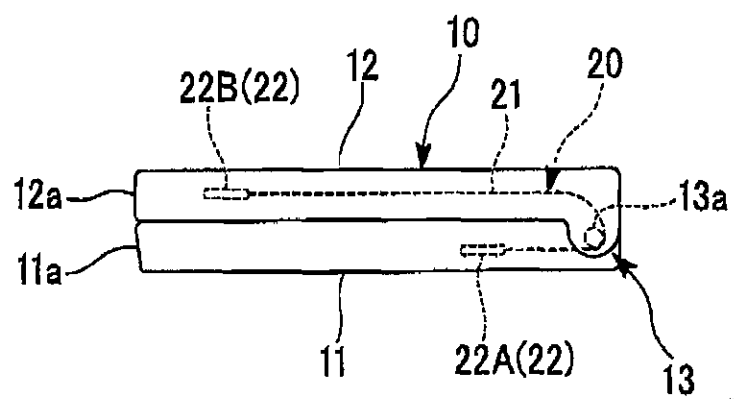


FIG. 7A

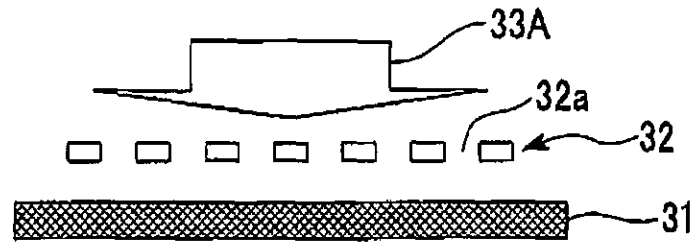


FIG. 7B

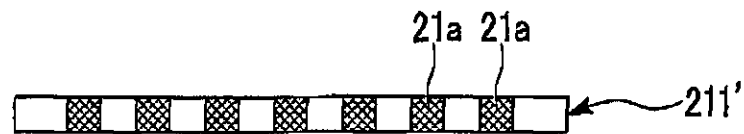


FIG. 7C

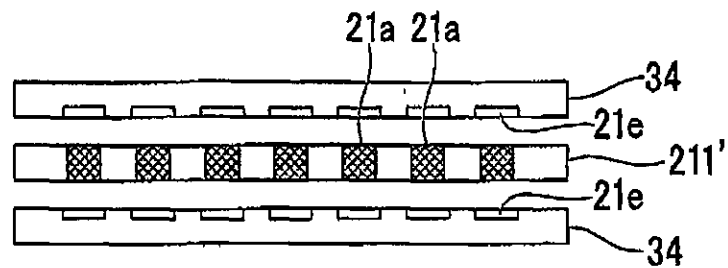


FIG. 7D

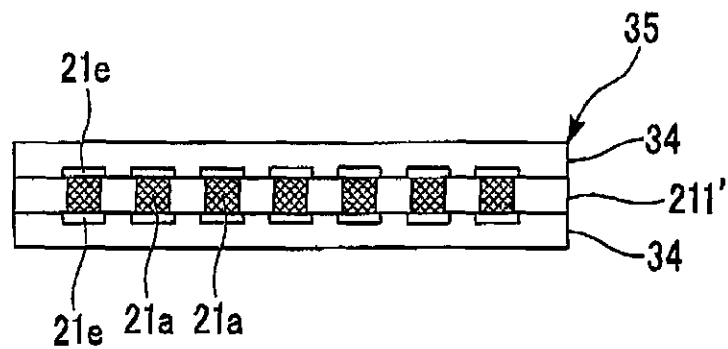


FIG. 7E

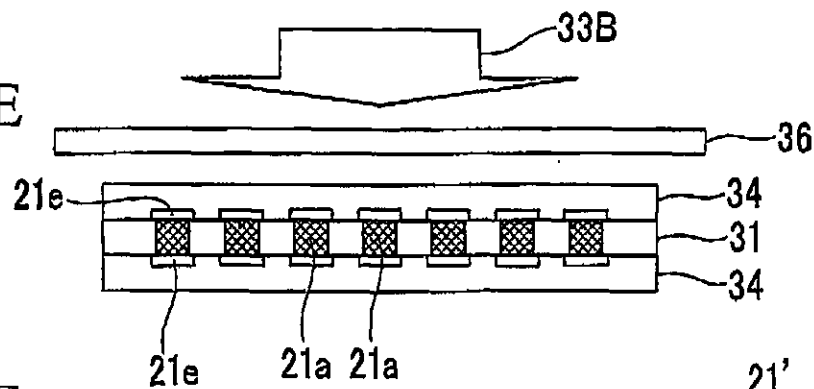


FIG. 7F

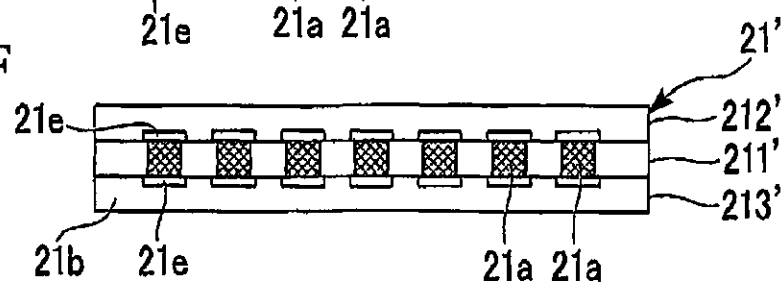


FIG. 8

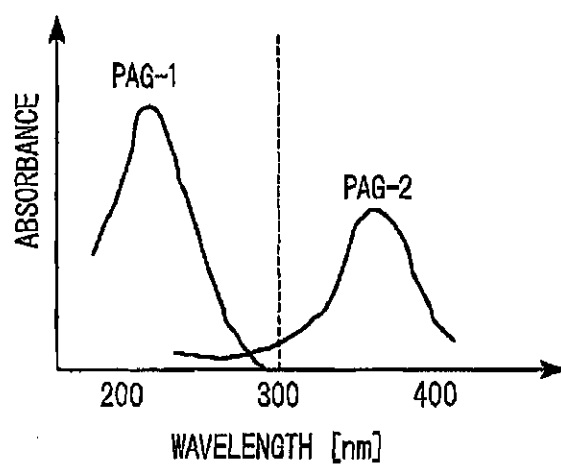


FIG. 9

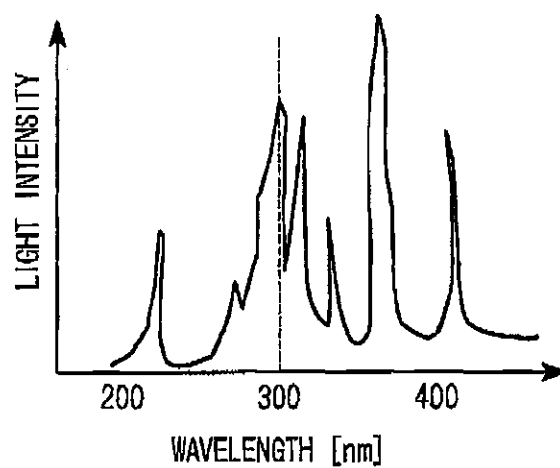


FIG. 10A

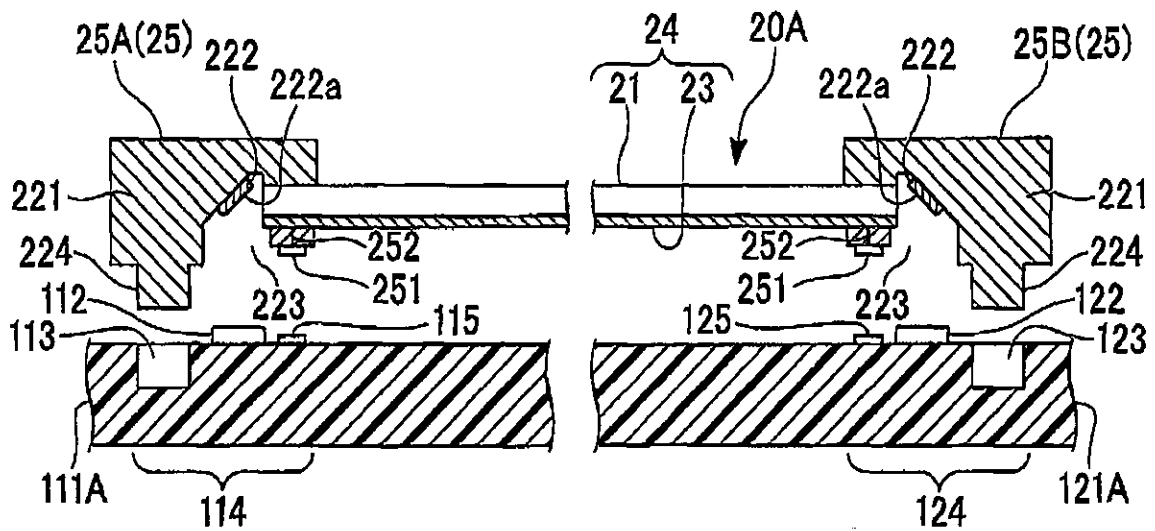


FIG. 10B

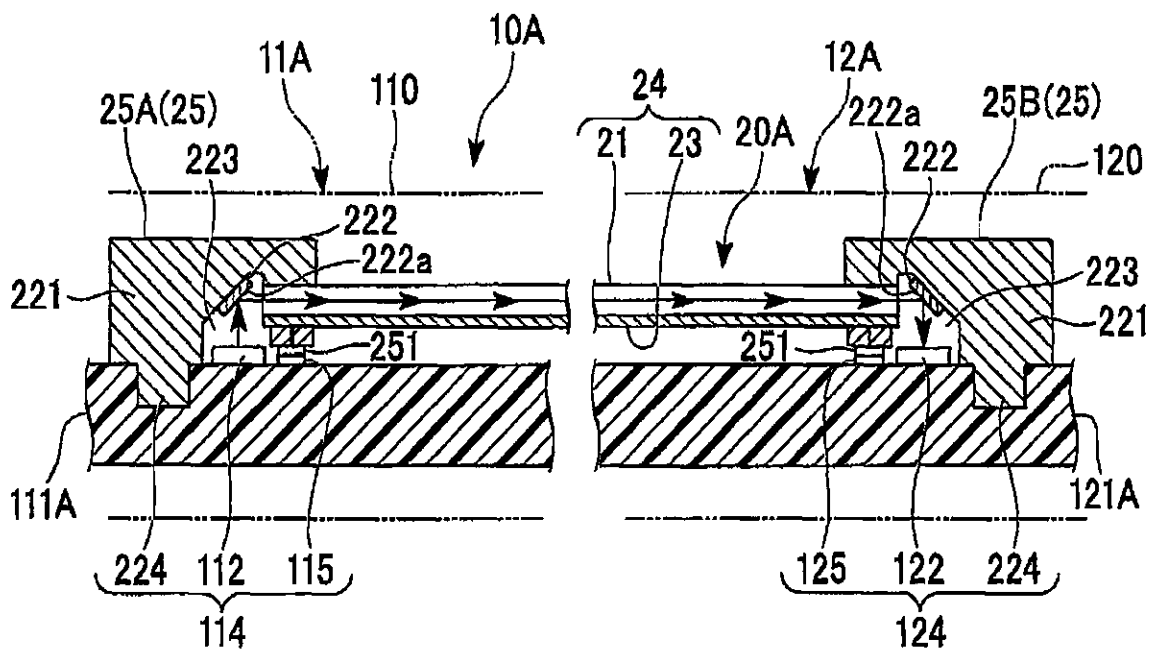


FIG. 11

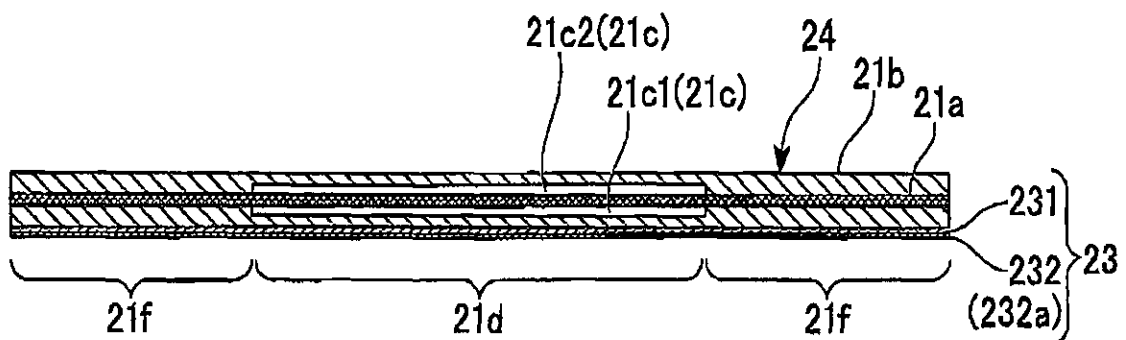


FIG. 12

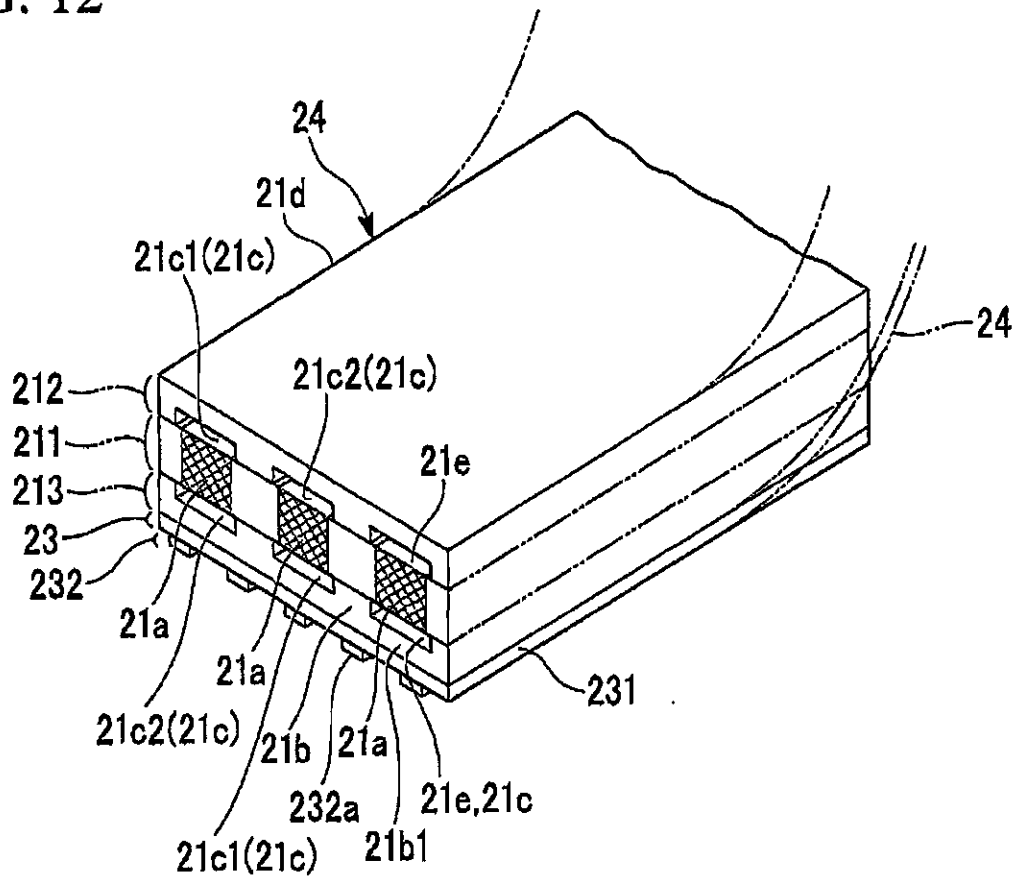


FIG. 13

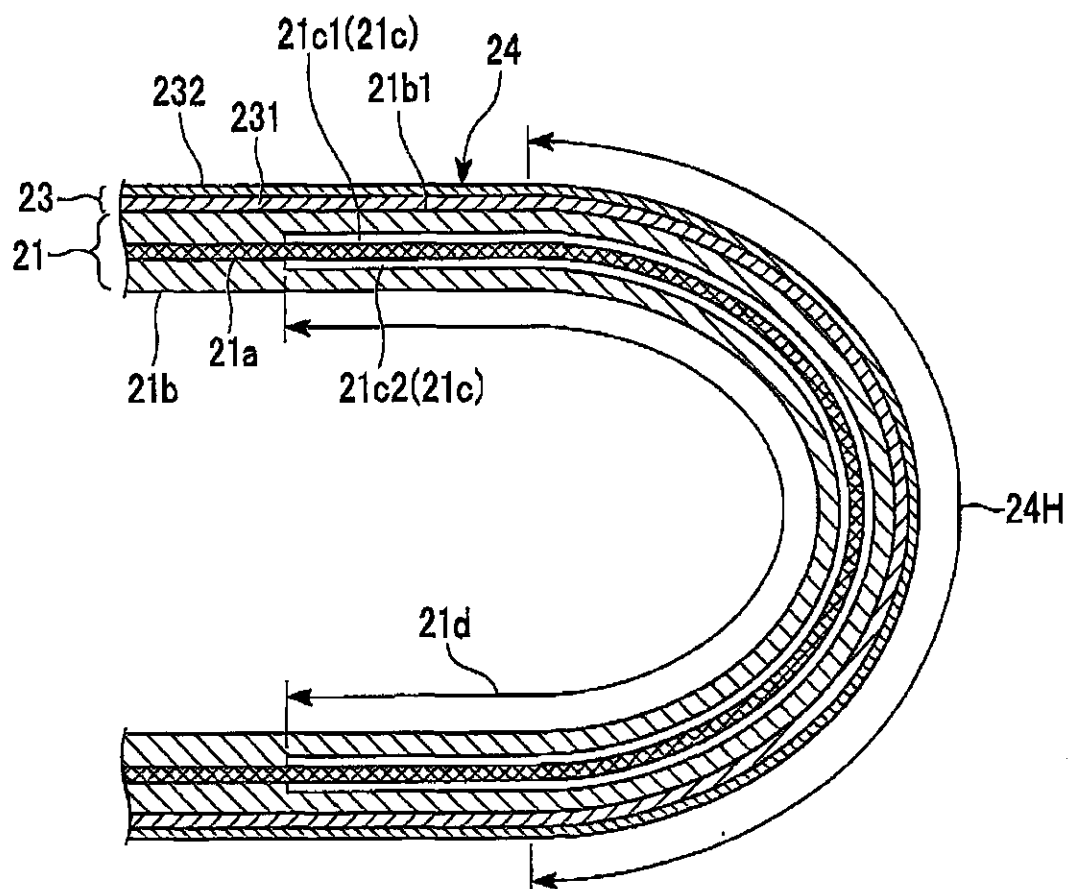


FIG. 14

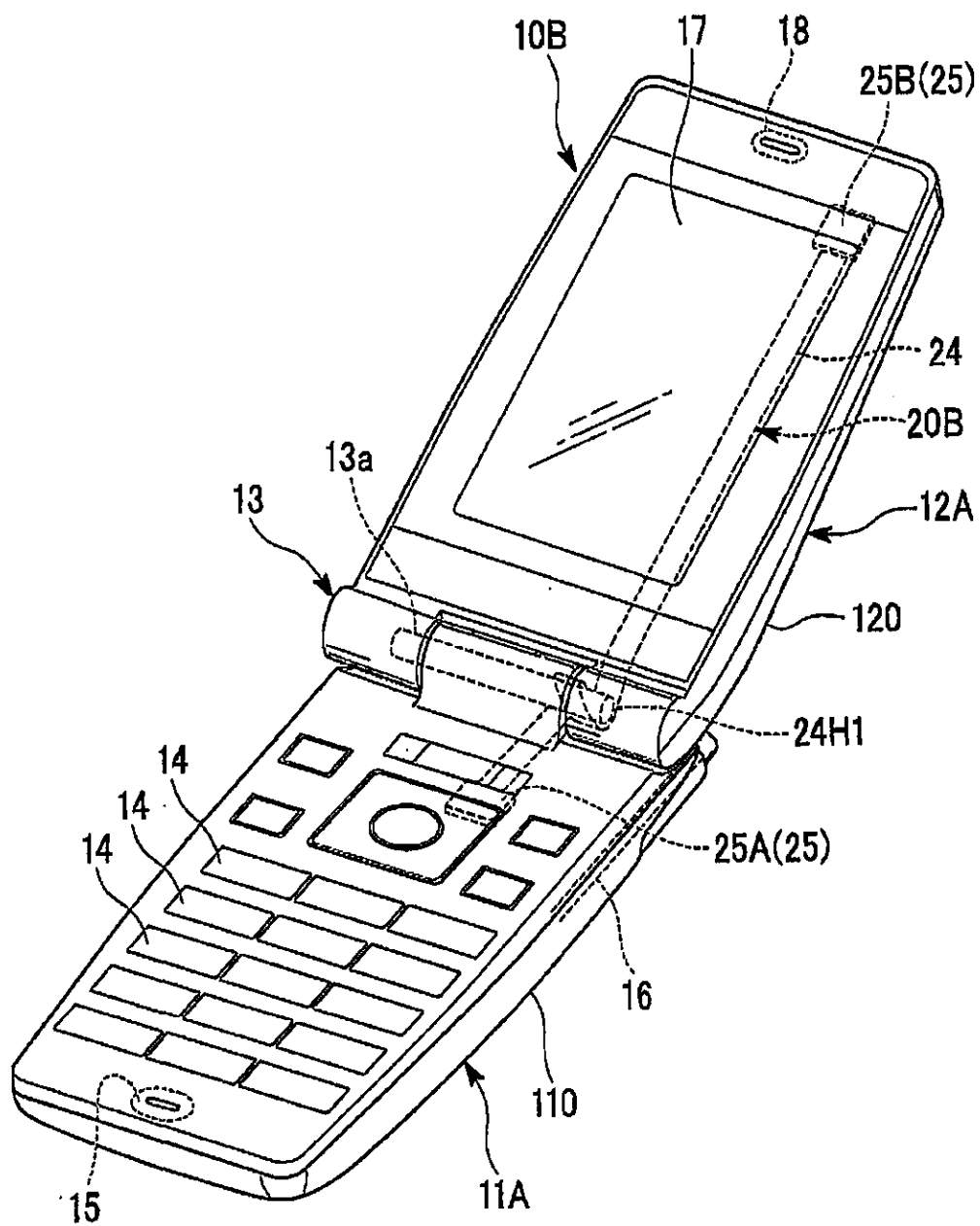


FIG. 15

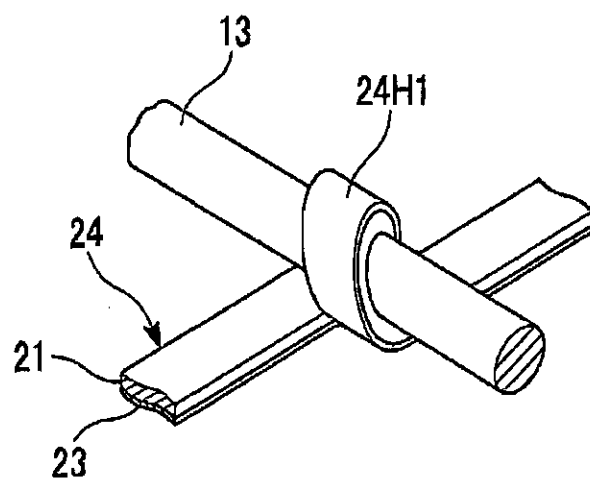


FIG. 16A

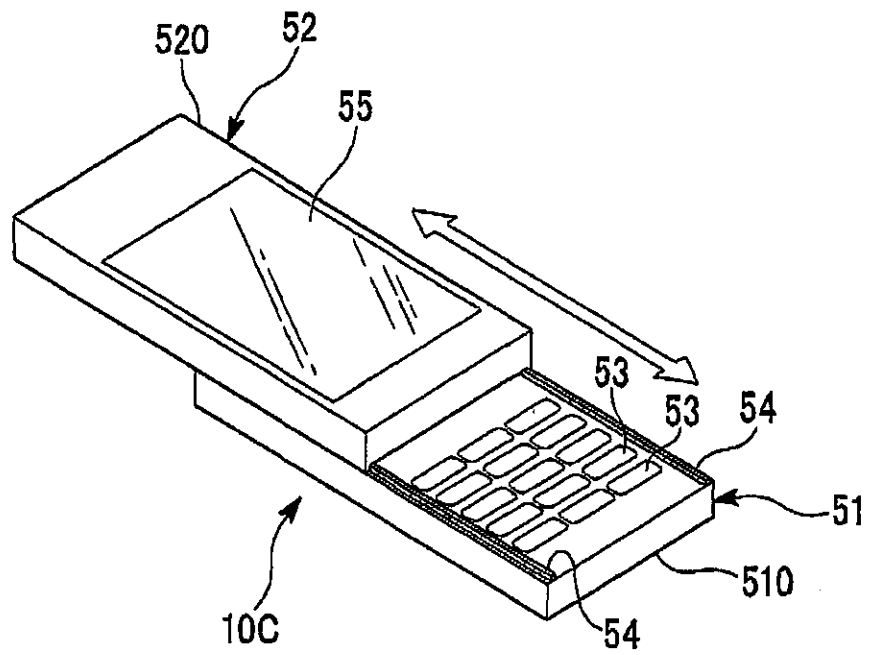


FIG. 16B

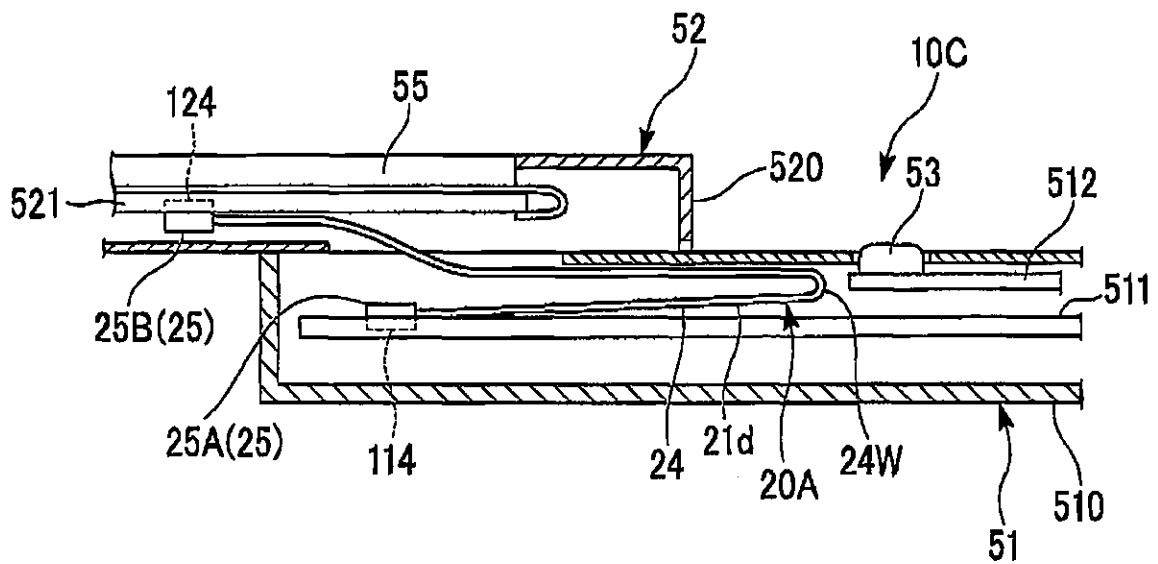


FIG. 16C

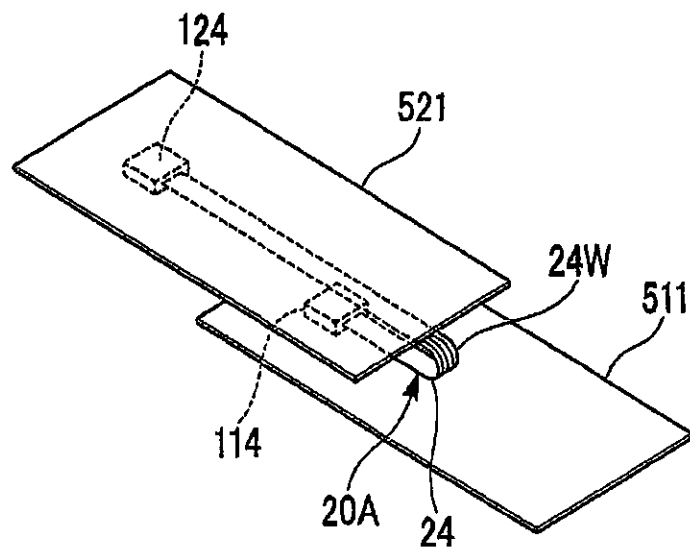


FIG. 17A

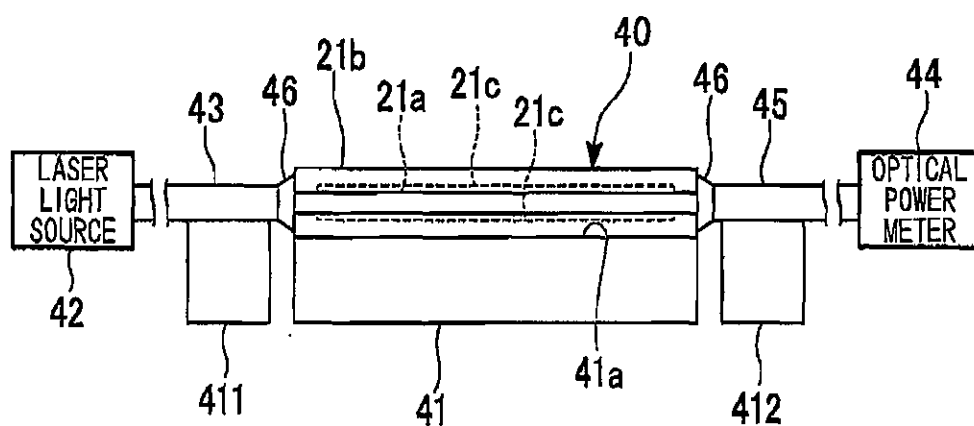


FIG. 17B

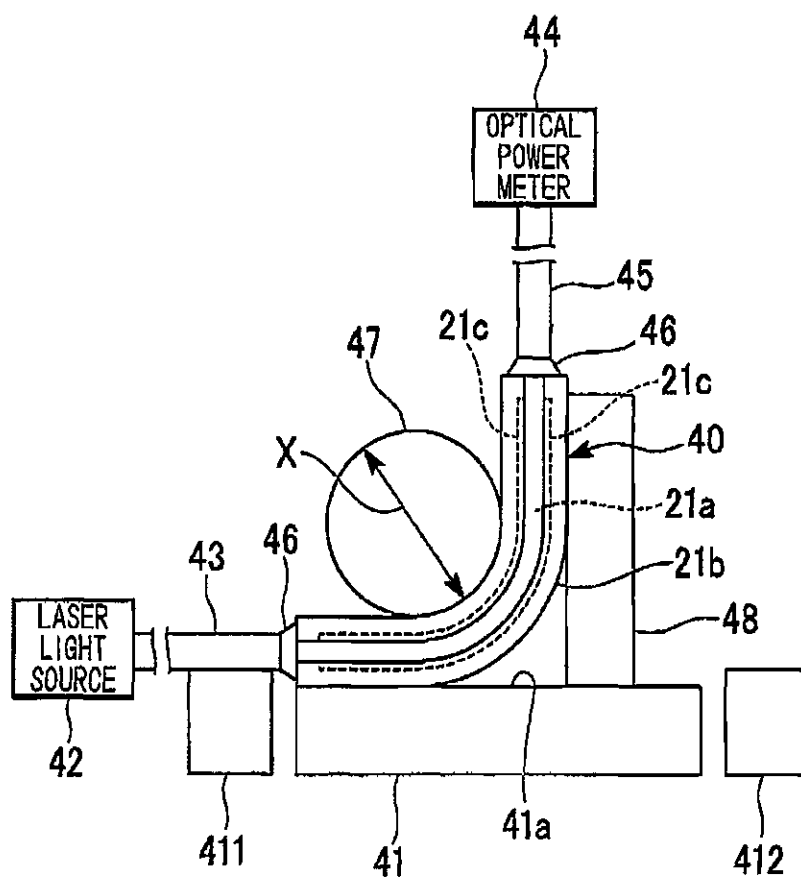


FIG. 18

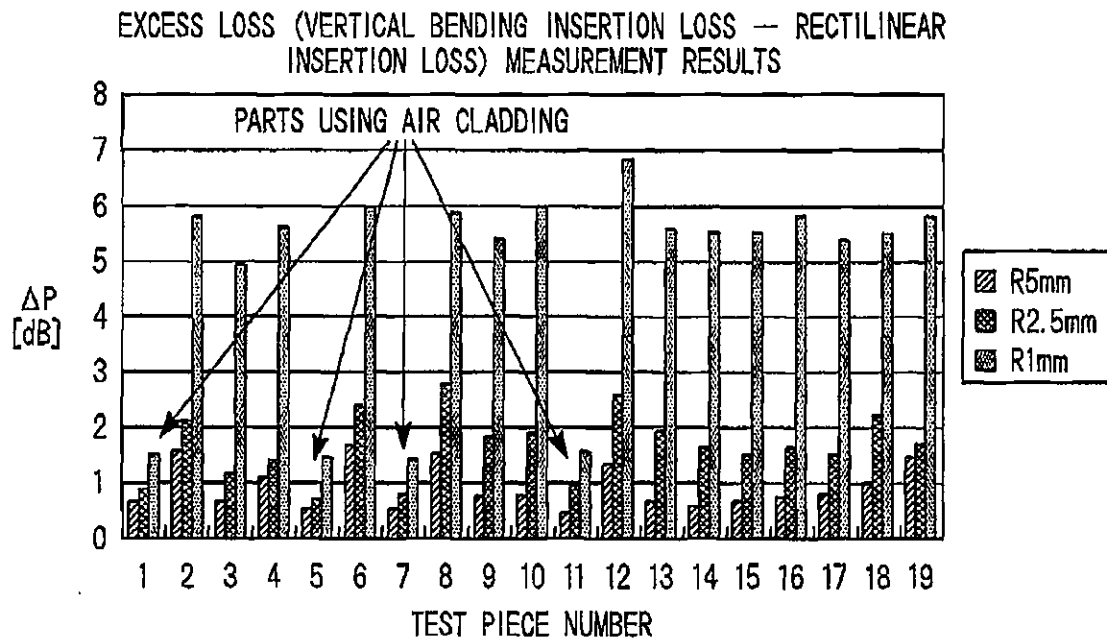


FIG. 19A

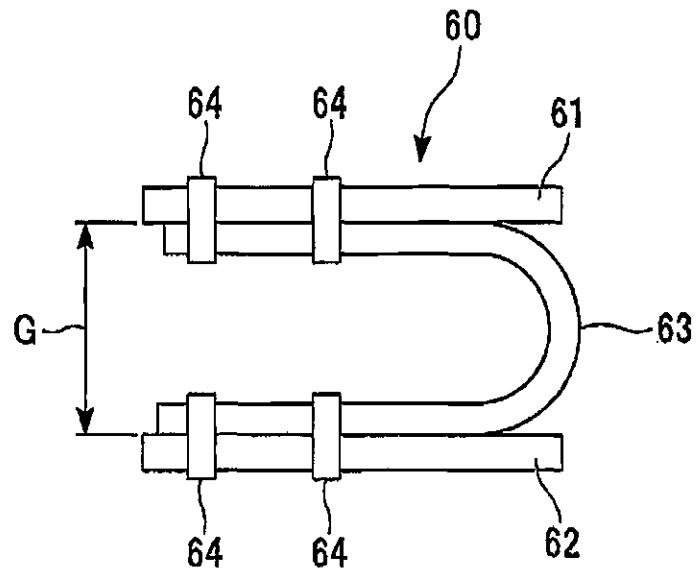


FIG. 19B

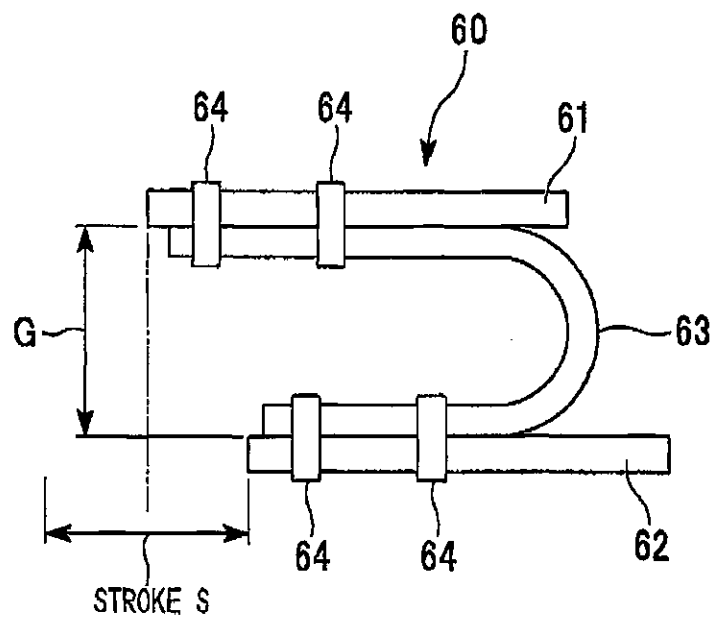


FIG. 20A

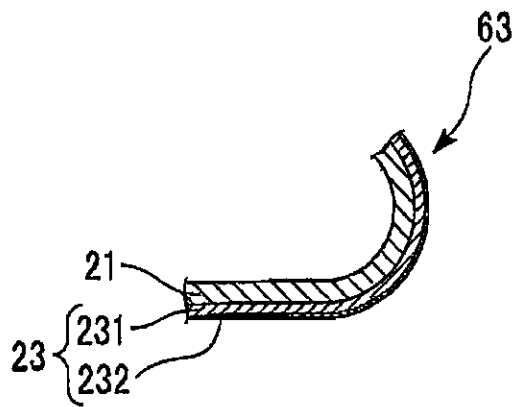


FIG. 20B

